

**CoolMOS™ Power Transistor**
**Features**

- Lowest figure-of-merit  $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Qualified for industrial grade applications according to JEDEC<sup>1)</sup>
- Pb-free lead plating; RoHS compliant; Halogen free mold compound

**Product Summary**

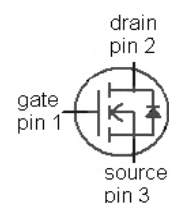
|                      |       |          |
|----------------------|-------|----------|
| $V_{DS} @ T_{j,max}$ | 650   | V        |
| $R_{DS(on),max}$     | 0.299 | $\Omega$ |
| $Q_{g,typ}$          | 22    | nC       |

**CoolMOS CP is specially designed for:**

Hard switching SMPS topologies

**PG-TO262**


| Type        | Package  | Ordering Code | Marking |
|-------------|----------|---------------|---------|
| IPI60R299CP | PG-TO262 | SP000103249   | 6R299P  |



**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                                               | Symbol            | Conditions                                | Value       | Unit |
|---------------------------------------------------------|-------------------|-------------------------------------------|-------------|------|
| Continuous drain current                                | $I_D$             | $T_C=25\text{ °C}$                        | 11          | A    |
|                                                         |                   | $T_C=100\text{ °C}$                       | 7           |      |
| Pulsed drain current <sup>2)</sup>                      | $I_{D,pulse}$     | $T_C=25\text{ °C}$                        | 34          |      |
| Avalanche energy, single pulse                          | $E_{AS}$          | $I_D=4.4\text{ A}$ , $V_{DD}=50\text{ V}$ | 290         | mJ   |
| Avalanche energy, repetitive $t_{AR}$ <sup>2),3)</sup>  | $E_{AR}$          | $I_D=4.4\text{ A}$ , $V_{DD}=50\text{ V}$ | 0.44        |      |
| Avalanche current, repetitive $t_{AR}$ <sup>2),3)</sup> | $I_{AR}$          |                                           | 4.4         | A    |
| MOSFET dv/dt ruggedness                                 | dv/dt             | $V_{DS}=0\ldots480\text{ V}$              | 50          | V/ns |
| Gate source voltage                                     | $V_{GS}$          | static                                    | $\pm 20$    | V    |
|                                                         |                   | AC ( $f>1\text{ Hz}$ )                    | $\pm 30$    |      |
| Power dissipation                                       | $P_{tot}$         | $T_C=25\text{ °C}$                        | 96          | W    |
| Operating and storage temperature                       | $T_j$ , $T_{stg}$ |                                           | -55 ... 150 | °C   |

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol        | Conditions         | Value | Unit |
|-------------------------------------|---------------|--------------------|-------|------|
| Continuous diode forward current    | $I_S$         | $T_C=25\text{ °C}$ | 6.6   | A    |
| Diode pulse current <sup>2)</sup>   | $I_{S,pulse}$ |                    | 34    |      |
| Reverse diode $dv/dt$ <sup>4)</sup> | $dv/dt$       |                    | 15    | V/ns |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                                            |            |                                       |   |   |     |     |
|------------------------------------------------------------|------------|---------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case                        | $R_{thJC}$ |                                       | - | - | 1.3 | K/W |
| Thermal resistance, junction - ambient                     | $R_{thJA}$ | leaded                                | - | - | 62  |     |
| Soldering temperature, wavesoldering only allowed at leads | $T_{sold}$ | 1.6 mm (0.063 in.) from case for 10 s | - | - | 260 | °C  |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |               |                                                             |     |      |       |               |
|----------------------------------|---------------|-------------------------------------------------------------|-----|------|-------|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$             | 600 | -    | -     | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=0.44\text{ mA}$                         | 2.5 | 3    | 3.5   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | -    | 1     | $\mu\text{A}$ |
|                                  |               | $V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$ | -   | 10   | -     |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                     | -   | -    | 100   | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=6.6\text{ A}, T_j=25\text{ °C}$    | -   | 0.27 | 0.299 | $\Omega$      |
|                                  |               | $V_{GS}=10\text{ V}, I_D=6.6\text{ A}, T_j=150\text{ °C}$   | -   | 0.73 |       |               |
| Gate resistance                  | $R_G$         | $f=1\text{ MHz}$ , open drain                               | -   | 1.9  | -     | $\Omega$      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                                                            |              |                                                                                        |   |      |   |    |
|------------------------------------------------------------|--------------|----------------------------------------------------------------------------------------|---|------|---|----|
| Input capacitance                                          | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$<br>$f=1\text{ MHz}$                          | - | 1100 | - | pF |
| Output capacitance                                         | $C_{oss}$    |                                                                                        | - | 60   | - |    |
| Effective output capacitance, energy related <sup>5)</sup> | $C_{o(er)}$  | $V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$<br>to 480 V                                     | - | 46   | - |    |
| Effective output capacitance, time related <sup>6)</sup>   | $C_{o(tr)}$  |                                                                                        | - | 120  | - |    |
| Turn-on delay time                                         | $t_{d(on)}$  | $V_{DD}=400\text{ V},$<br>$V_{GS}=10\text{ V}, I_D=6.6\text{ A},$<br>$R_G=4.3\ \Omega$ | - | 10   | - | ns |
| Rise time                                                  | $t_r$        |                                                                                        | - | 5    | - |    |
| Turn-off delay time                                        | $t_{d(off)}$ |                                                                                        | - | 40   | - |    |
| Fall time                                                  | $t_f$        |                                                                                        | - | 5    | - |    |

**Gate Charge Characteristics**

|                       |               |                                                                              |   |     |    |    |
|-----------------------|---------------|------------------------------------------------------------------------------|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=400\text{ V}, I_D=6.6\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 5   | -  | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                              | - | 7.6 | -  |    |
| Gate charge total     | $Q_g$         |                                                                              | - | 22  | 29 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                              | - | 5.0 | -  | V  |

**Reverse Diode**

|                               |           |                                                                    |   |     |     |               |
|-------------------------------|-----------|--------------------------------------------------------------------|---|-----|-----|---------------|
| Diode forward voltage         | $V_{SD}$  | $V_{GS}=0\text{ V}, I_F=6.6\text{ A},$<br>$T_j=25\text{ °C}$       | - | 0.9 | 1.2 | V             |
| Reverse recovery time         | $t_{rr}$  | $V_R=400\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 300 | -   | ns            |
| Reverse recovery charge       | $Q_{rr}$  |                                                                    | - | 3.9 | -   | $\mu\text{C}$ |
| Peak reverse recovery current | $I_{rrm}$ |                                                                    | - | 26  | -   | A             |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

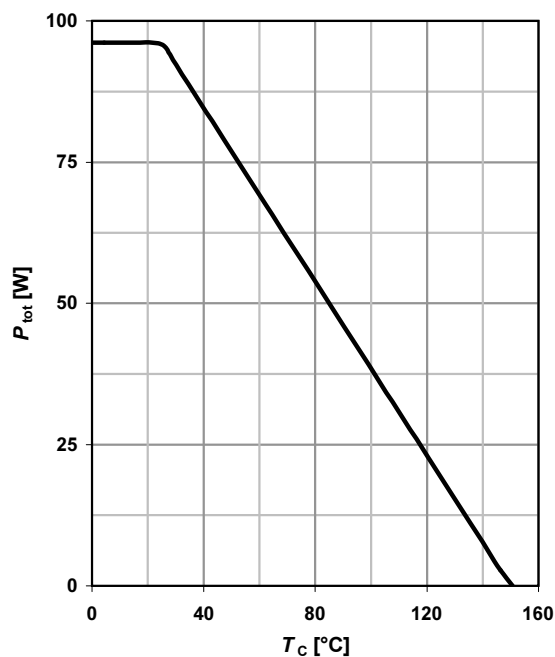
<sup>4)</sup>  $I_{SD} \leq I_D$ ,  $di/dt \leq 200\text{ A}/\mu\text{s}$ ,  $V_{DClk}=400\text{ V}$ ,  $V_{peak} < V_{(BR)DSS}$ ,  $T_j < T_{j,max}$ , identical low side and high side switch.

<sup>5)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>6)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

## 1 Power dissipation

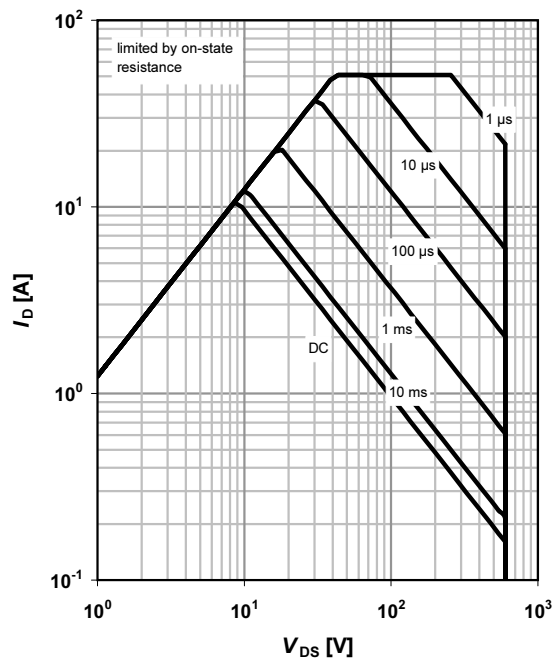
$$P_{\text{tot}} = f(T_C)$$



## 2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

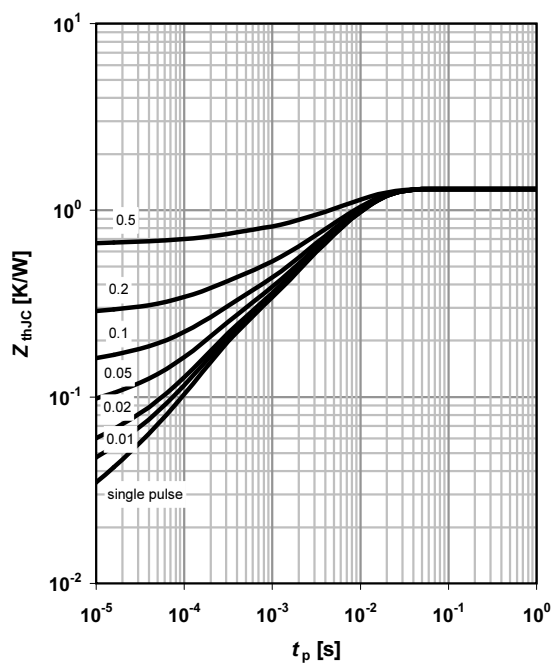
parameter:  $t_p$



## 3 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

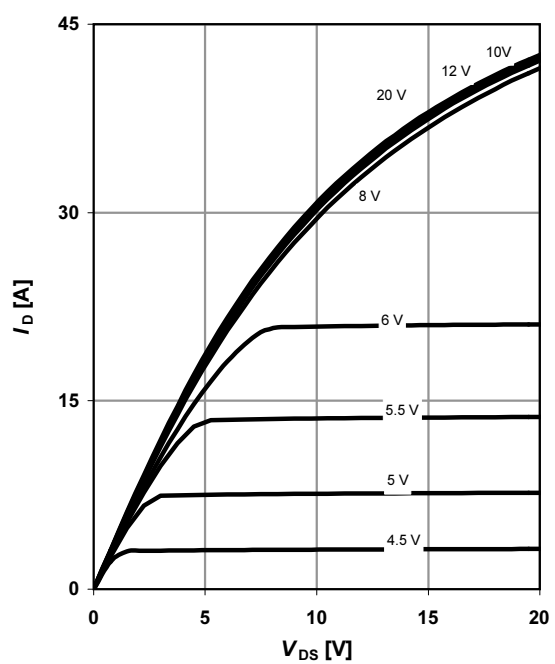
parameter:  $D = t_p / T$



## 4 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

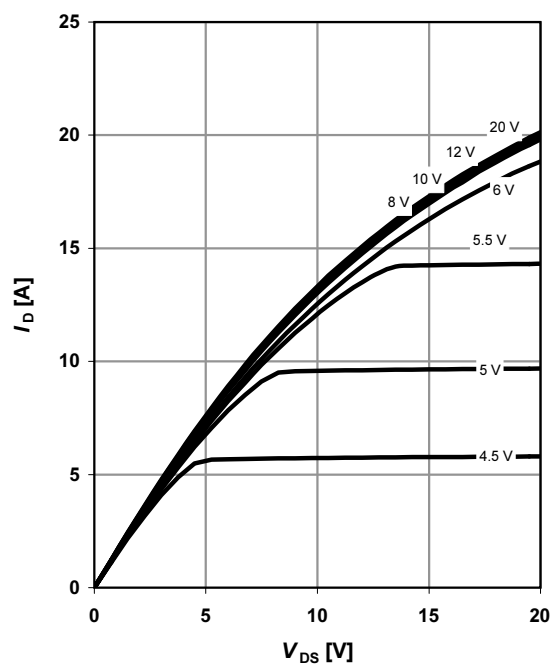
parameter:  $V_{GS}$



## 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 150^\circ\text{C}$$

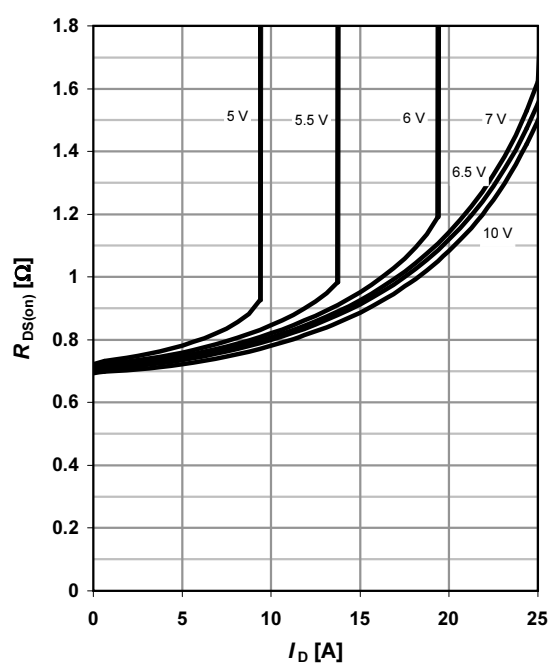
parameter:  $V_{GS}$



## 6 Typ. drain-source on-state resistance

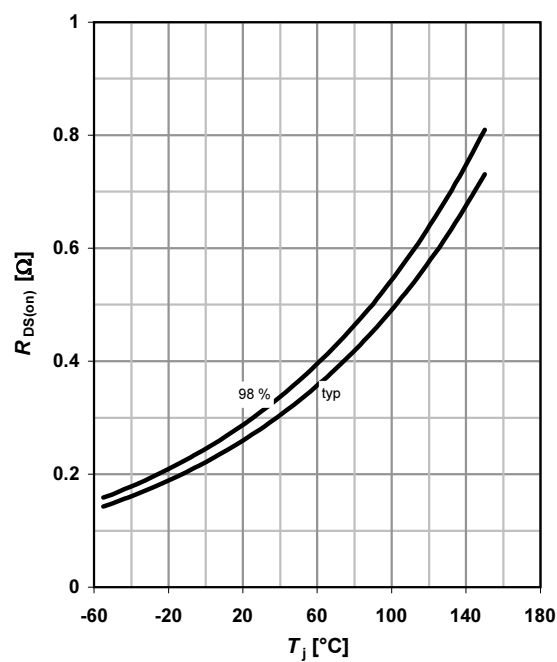
$$R_{DS(on)} = f(I_D); T_J = 150^\circ\text{C}$$

parameter:  $V_{GS}$



## 7 Drain-source on-state resistance

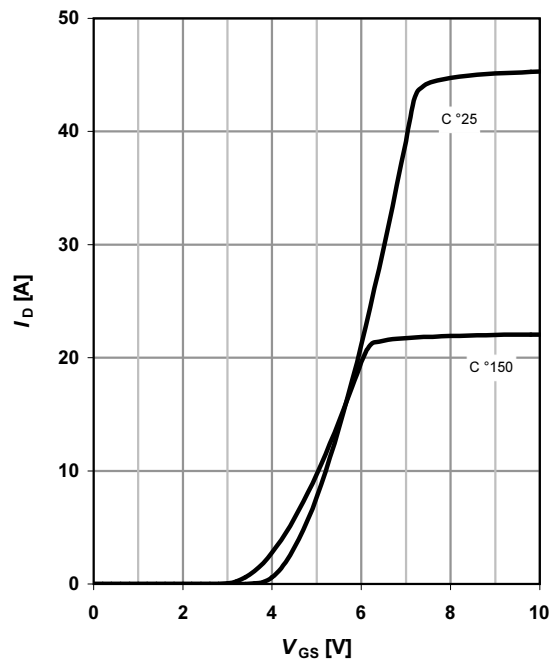
$$R_{DS(on)} = f(T_J); I_D = 6.6\text{ A}; V_{GS} = 10\text{ V}$$



## 8 Typ. transfer characteristics

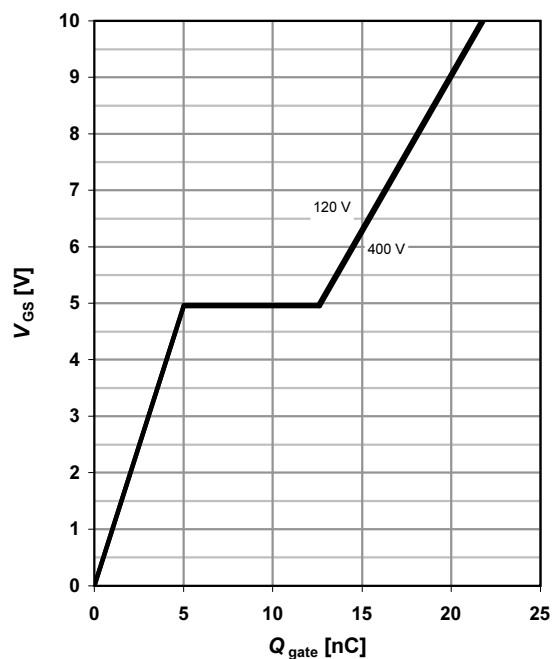
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)\text{max}}$$

parameter:  $T_J$



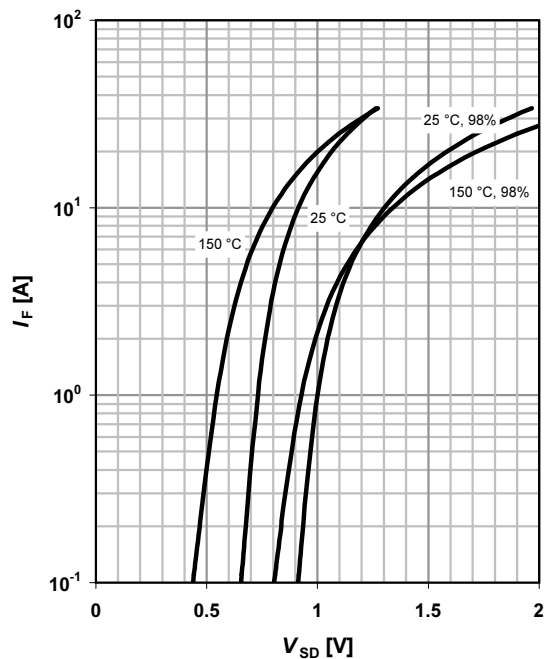
## 9 Typ. gate charge

 $V_{GS}=f(Q_{gate}); I_D=6.6 \text{ A pulsed}$ 

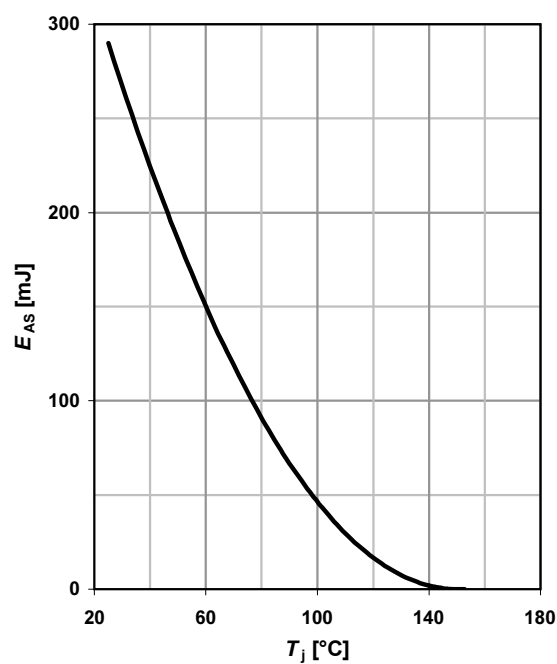
parameter:  $V_{DD}$ 


## 10 Forward characteristics of reverse diode

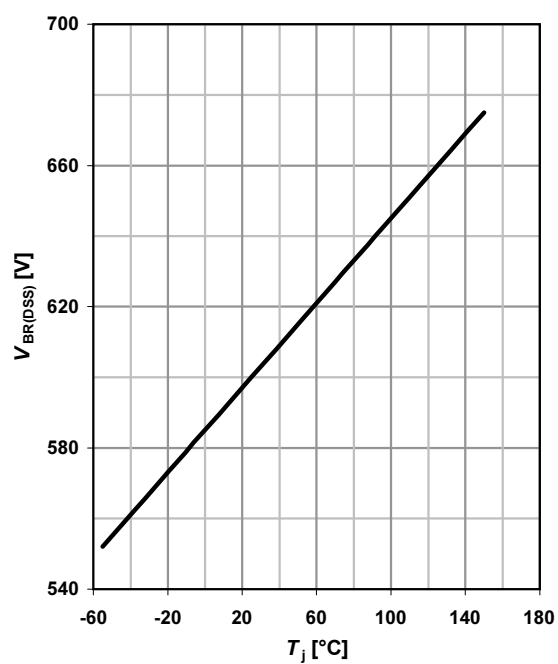
 $I_F=f(V_{SD})$ 

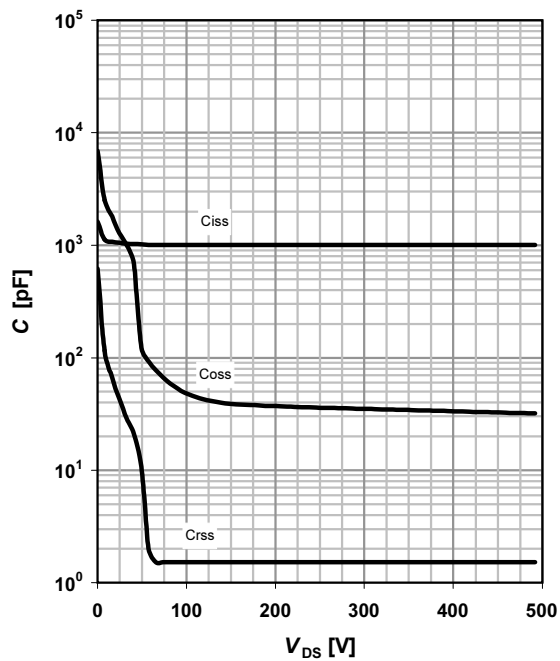
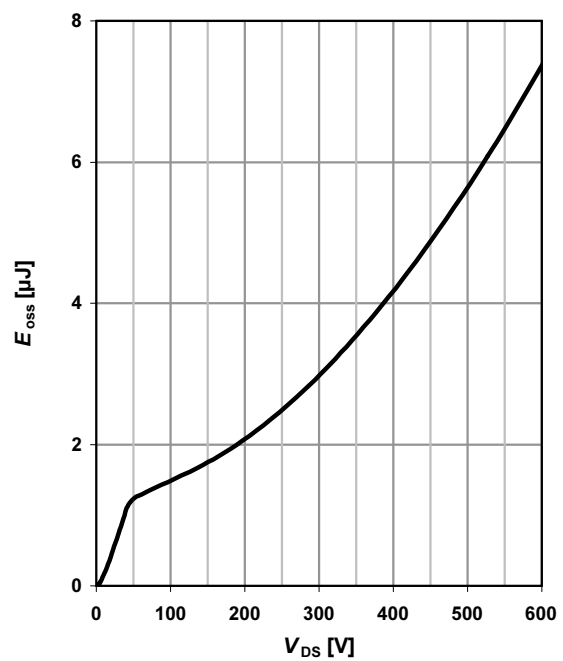
parameter:  $T_j$ 


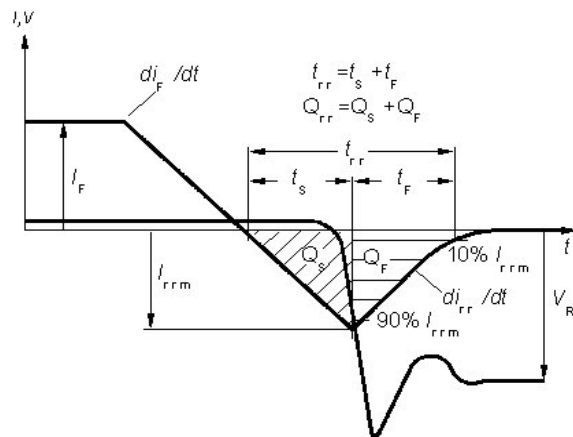
## 11 Avalanche energy

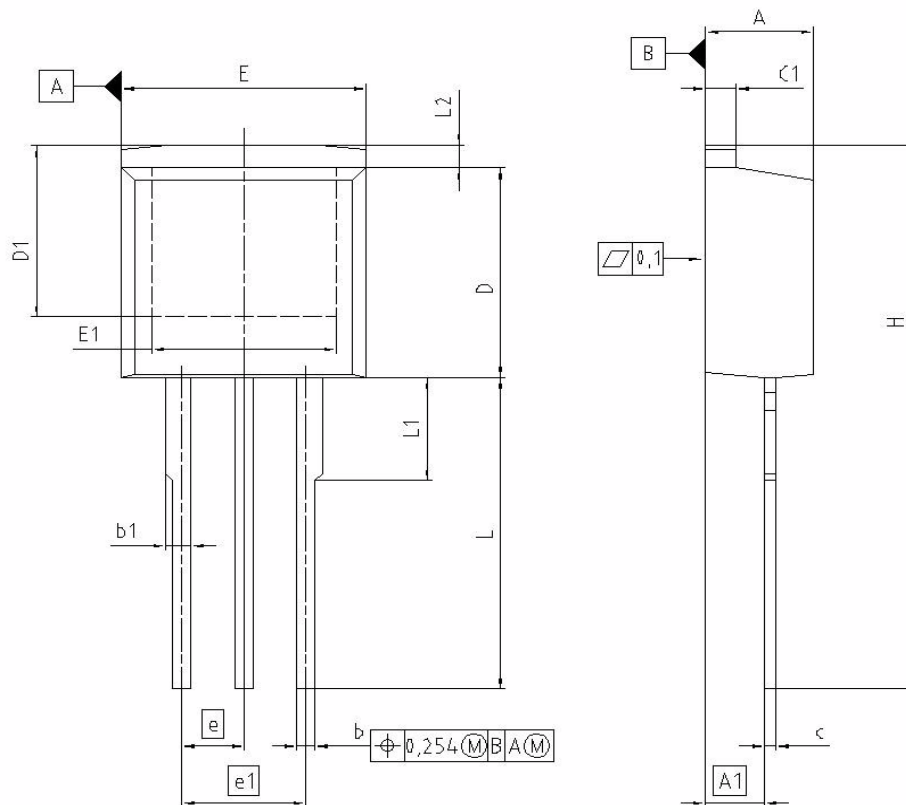
 $E_{AS}=f(T_j); I_D=4.4 \text{ A}; V_{DD}=50 \text{ V}$ 


## 12 Drain-source breakdown voltage

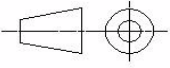
 $V_{BR(DSS)}=f(T_j); I_D=0.25 \text{ mA}$ 


**13 Typ. capacitances**
 $C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$ 

**14 Typ. Coss stored energy**
 $E_{oss} = f(V_{DS})$ 


**Definition of diode switching characteristics**


**PG-TO262-3-1: Outlines**


| DIM       | MILLIMETERS |        | INCHES |       |
|-----------|-------------|--------|--------|-------|
|           | MIN         | MAX    | MIN    | MAX   |
| <b>A</b>  | 4.300       | 4.500  | 0.169  | 0.177 |
| <b>A1</b> | 2.150       | 2.650  | 0.085  | 0.104 |
| <b>b</b>  | 0.650       | 0.850  | 0.026  | 0.033 |
| <b>b1</b> | 0.635       | 1.400  | 0.025  | 0.055 |
| <b>c</b>  | 0.400       | 0.600  | 0.016  | 0.024 |
| <b>c1</b> | 1.170       | 1.370  | 0.046  | 0.054 |
| <b>D</b>  | 9.050       | 9.450  | 0.356  | 0.372 |
| <b>D1</b> | 6.900       | 7.650  | 0.272  | 0.301 |
| <b>E</b>  | 9.800       | 10.200 | 0.386  | 0.402 |
| <b>E1</b> | 7.250       | 8.600  | 0.285  | 0.339 |
| <b>e</b>  | 2.540       |        | 0.100  |       |
| <b>e1</b> | 5.080       |        | 0.200  |       |
| <b>N</b>  | 3           |        | 3      |       |
| <b>L</b>  | 13.000      | 14.000 | 0.512  | 0.551 |
| <b>L1</b> | 4.350       | 4.750  | 0.171  | 0.187 |
| <b>L2</b> | 0.700       | 1.300  | 0.028  | 0.051 |

|                                                                                                                     |
|---------------------------------------------------------------------------------------------------------------------|
| <b>REFERENCE</b><br>JEDEC TO262                                                                                     |
| <b>SCALE</b><br>0 2.5 5mm                                                                                           |
| <b>EUROPEAN PROJECTION</b><br> |
| <b>ISSUE DATE</b><br>01-06-2005                                                                                     |
| <b>FILE</b><br>TO262_1                                                                                              |

Dimensions in mm/inches

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